

# FDP51N25 / FDPF51N25 250V N-Channel MOSFET

## Features

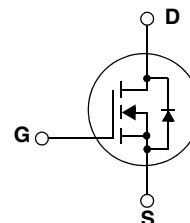
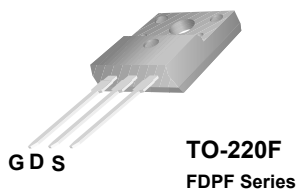
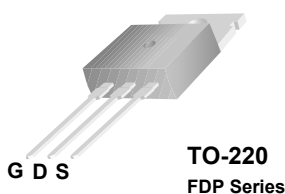
- 51A, 250V,  $R_{DS(on)} = 0.06\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 55 nC)
- Low Crss ( typical 63 pF)
- Fast switching
- Improved dv/dt capability



## Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.



## Absolute Maximum Ratings

Symbol	Parameter	FDP51N25	FDPF51N25	Unit	
$V_{DSS}$	Drain-Source Voltage	250		V	
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	51	51*	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	30	30*	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	204	204*	A	
$V_{GSS}$	Gate-Source voltage	$\pm 30$		V	
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1111		mJ	
$I_{AR}$	Avalanche Current (Note 1)	51		A	
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	32		mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns	
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	320	38	W	
		3.7	0.3	W/ $^\circ\text{C}$	
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$	
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$	

\*Drain current limited by maximum junction temperature

## Thermal Characteristics

Symbol	Parameter	FDP51N25	FDPF51N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.39	3.3	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C}/\text{W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP51N25	FDP51N25	TO-220	-	-	50
FDPF51N25	FDPF51N25	TO-220F	-	-	50

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

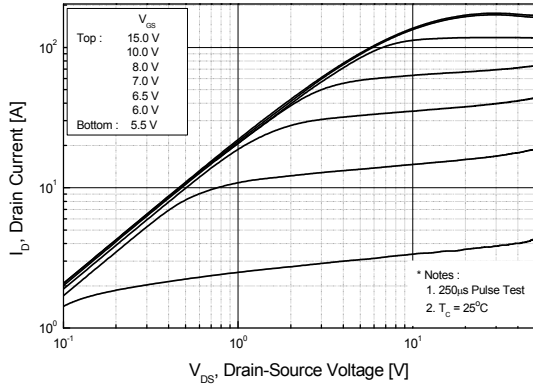
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA, T <sub>J</sub> = 25°C	250	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	--	0.25	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 250V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 200V, T <sub>C</sub> = 125°C	--	--	1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3.0	--	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25.5A	--	0.048	0.060	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40V, I <sub>D</sub> = 25.5A (Note 4)	--	43	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	--	2620	3410	pF
C <sub>oss</sub>	Output Capacitance		--	530	690	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	63	90	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125V, I <sub>D</sub> = 51A R <sub>G</sub> = 25Ω  (Note 4, 5)	--	62	135	ns
t <sub>r</sub>	Turn-On Rise Time		--	465	940	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	98	205	ns
t <sub>f</sub>	Turn-Off Fall Time		--	130	270	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 200V, I <sub>D</sub> = 51A V <sub>GS</sub> = 10V  (Note 4, 5)	--	55	70	nC
Q <sub>gs</sub>	Gate-Source Charge		--	16	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	27	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	51	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	204	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 51A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 51A di <sub>f</sub> /dt = 100A/μs  (Note 4)	--	178	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	4.0	--	μC

### Notes:

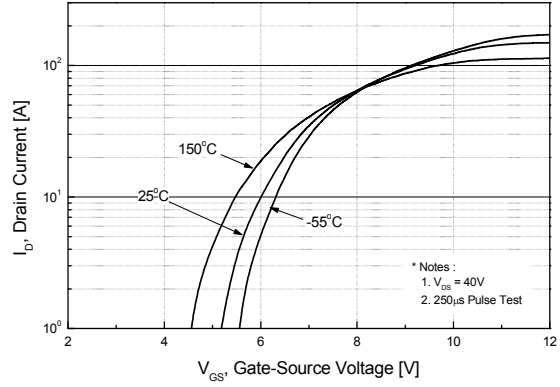
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 0.68mH, I<sub>AS</sub> = 51A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 51A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

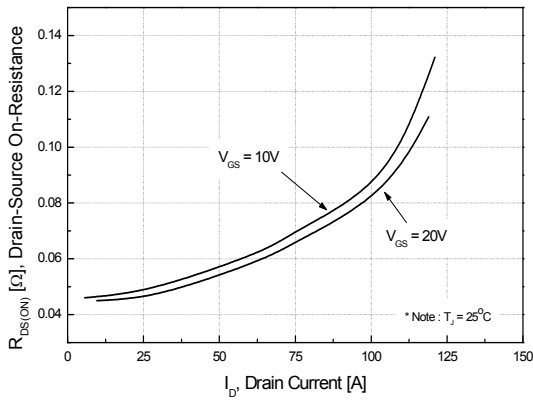
**Figure 1. On-Region Characteristics**



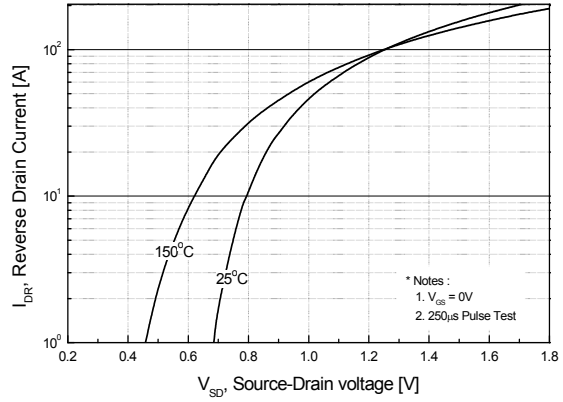
**Figure 2. Transfer Characteristics**



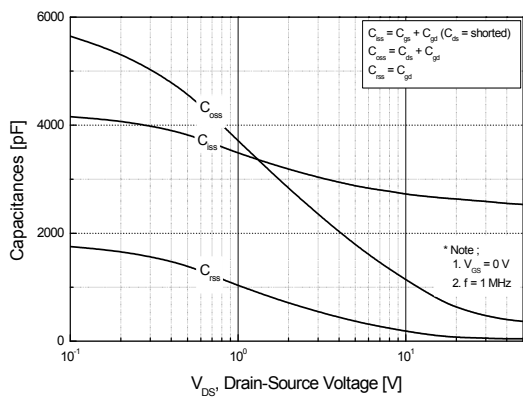
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



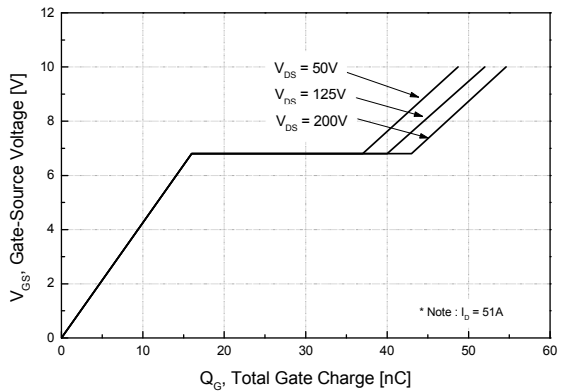
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

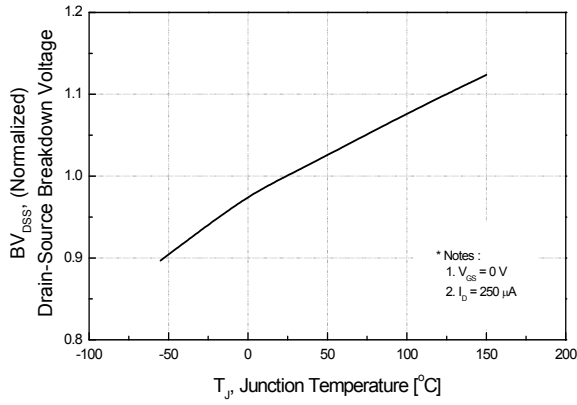


**Figure 6. Gate Charge Characteristics**

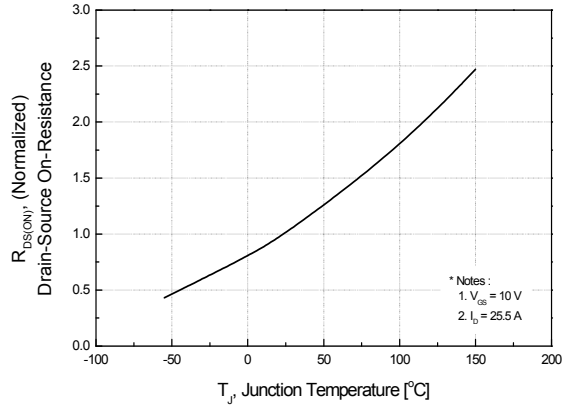


**Typical Performance Characteristics** (Continued)

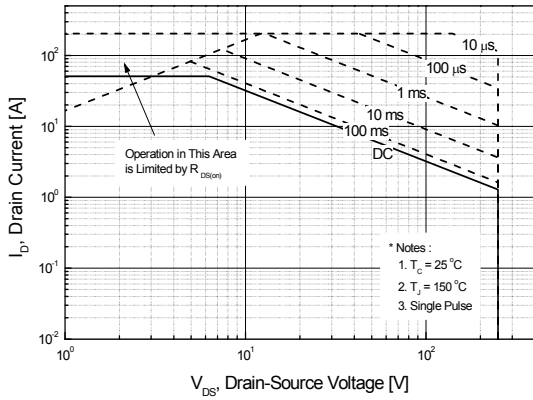
**Figure 7. Breakdown Voltage Variation vs. Temperature**



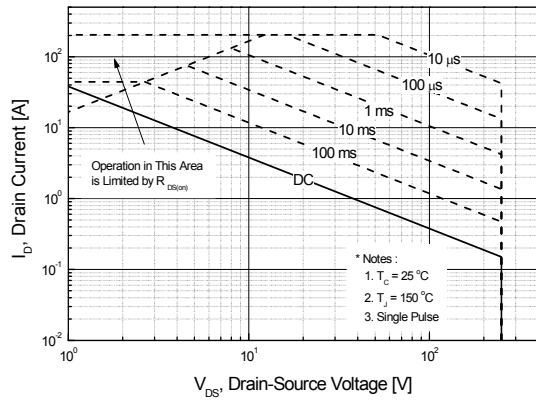
**Figure 8. On-Resistance Variation vs. Temperature**



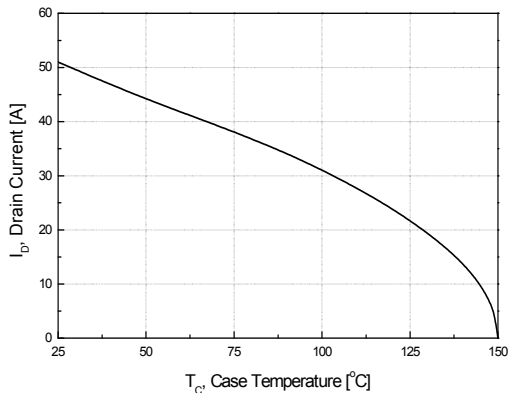
**Figure 9-1. Maximum Safe Operating Area for FDP51N25**



**Figure 9-2. Maximum Safe Operating Area for FDPF51N25**

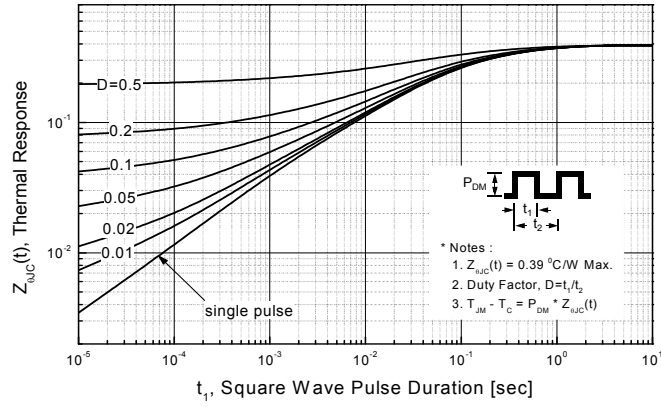


**Figure 10. Maximum Drain Current vs. Case Temperature**

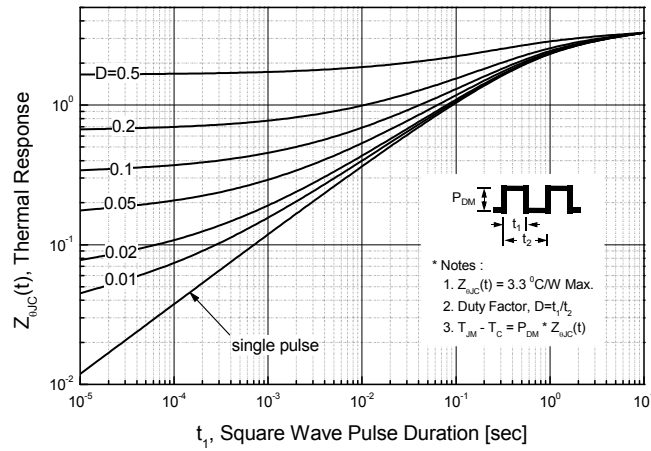


**Typical Performance Characteristics** (Continued)

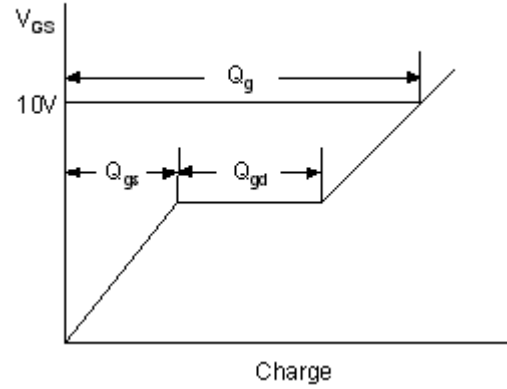
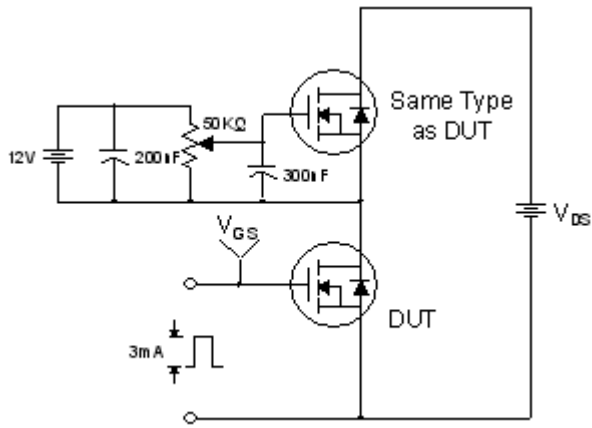
**Figure 11-1. Transient Thermal Response Curve for FDP51N25**



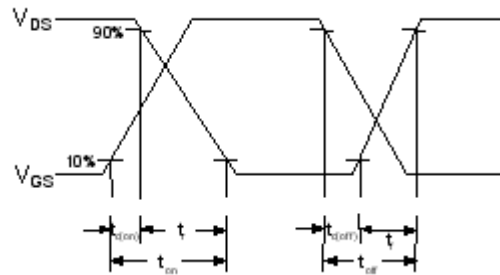
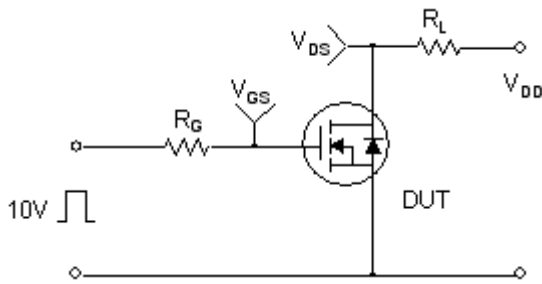
**Figure 11-2. Transient Thermal Response Curve for FDPF51N25**



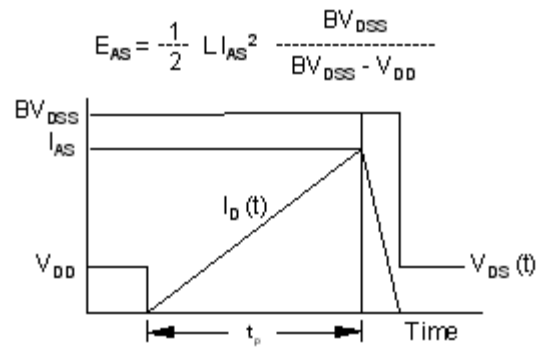
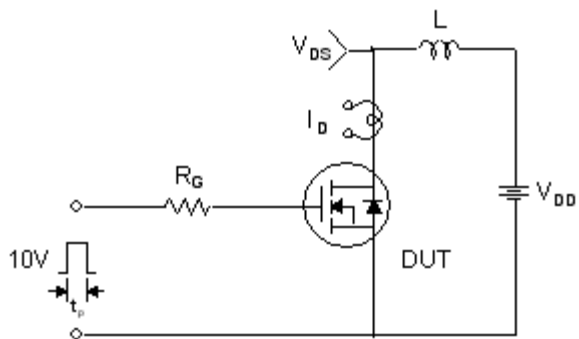
**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

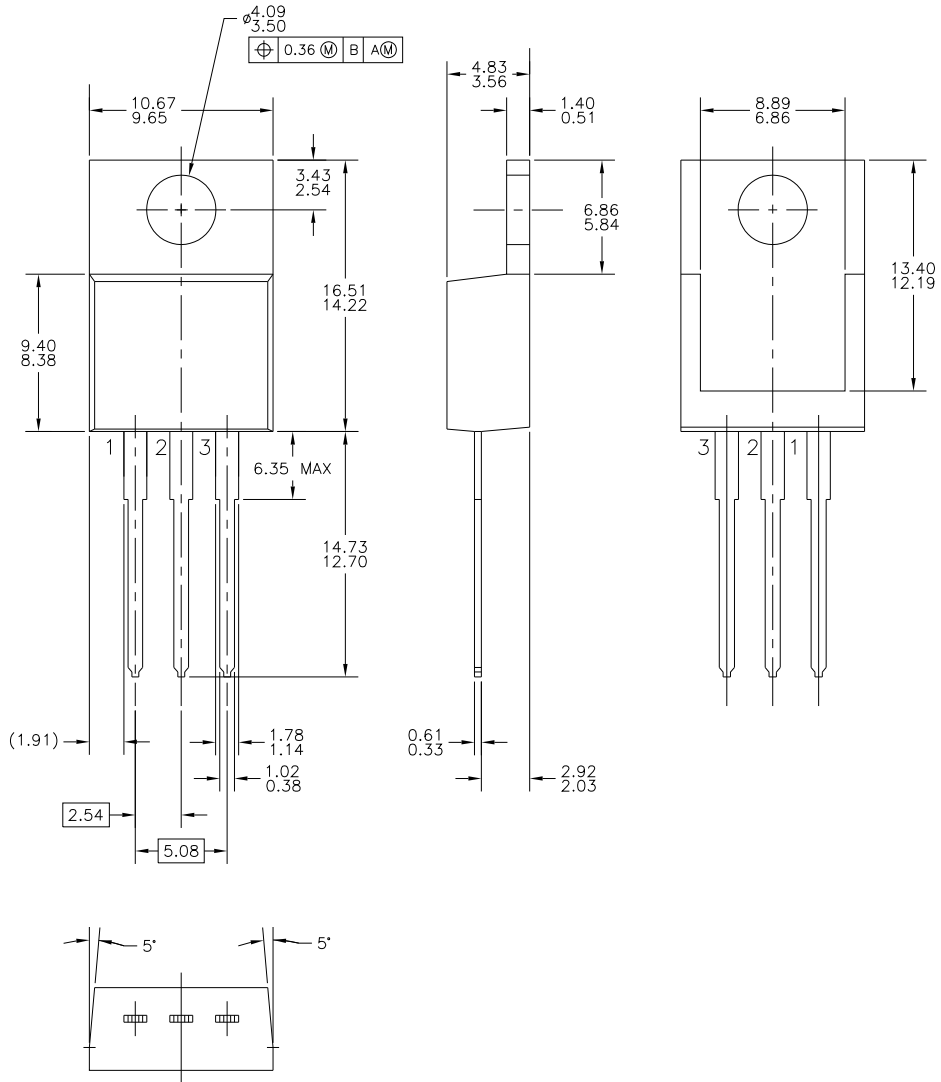


**Peak Diode Recovery dv/dt Test Circuit & Waveforms**



Mechanical Dimensions

TO-220

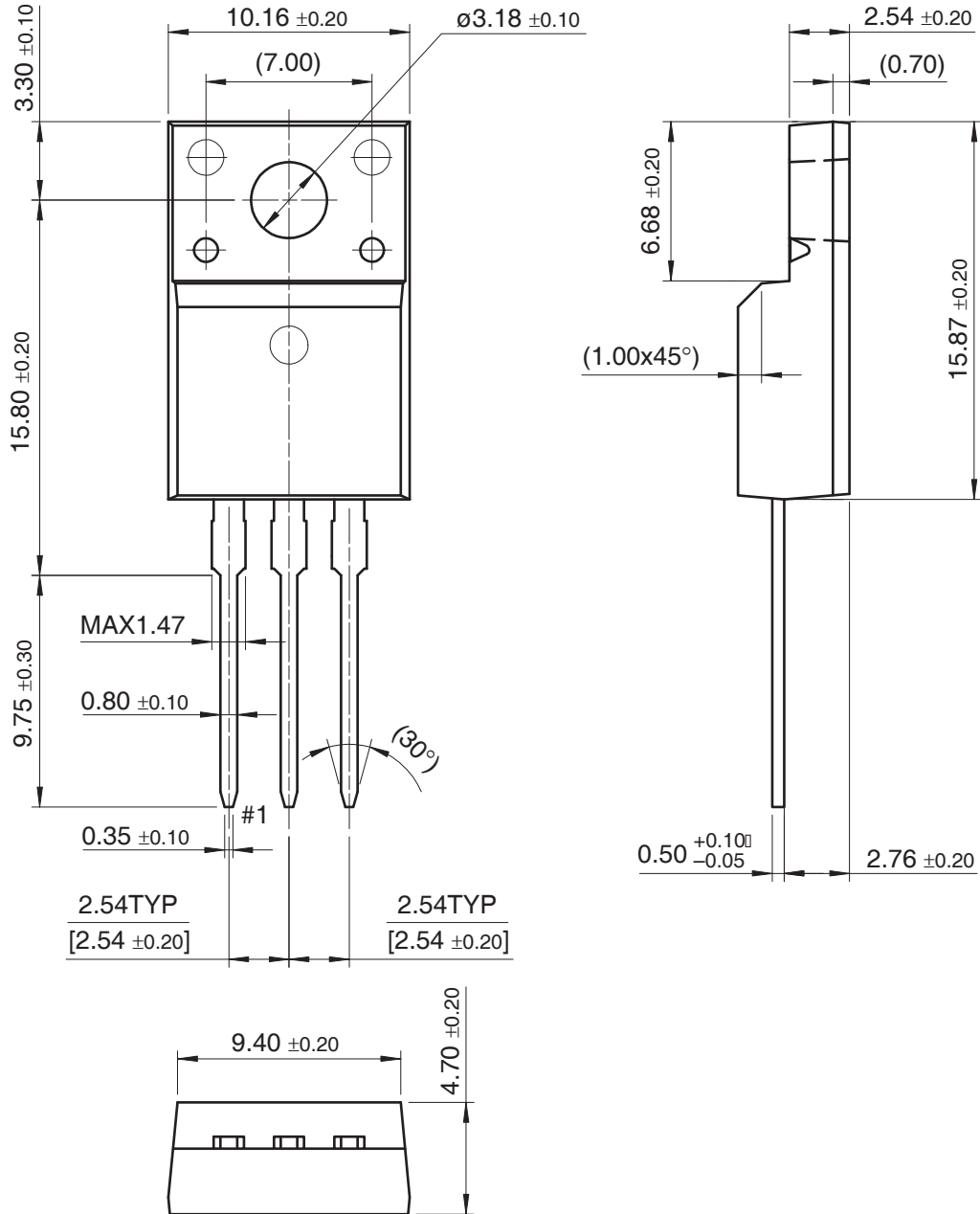


Dimensions in Millimeters



Mechanical Dimensions (Continued)

TO-220F



Dimensions in Millimeters



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